

PDFN5×6A MOS
Complementary Enhancement MOSFET in a PDFN5 × 6A Plastic Package.

N-channel

 $V_{DS}(V)=30V$ $I_D=39.5A$ $R_{DS(ON)}<10m\Omega(V_{GS}=10V)$ $R_{DS(ON)}<15m\Omega(V_{GS}=4.5V)$

HF Product.

P-channel

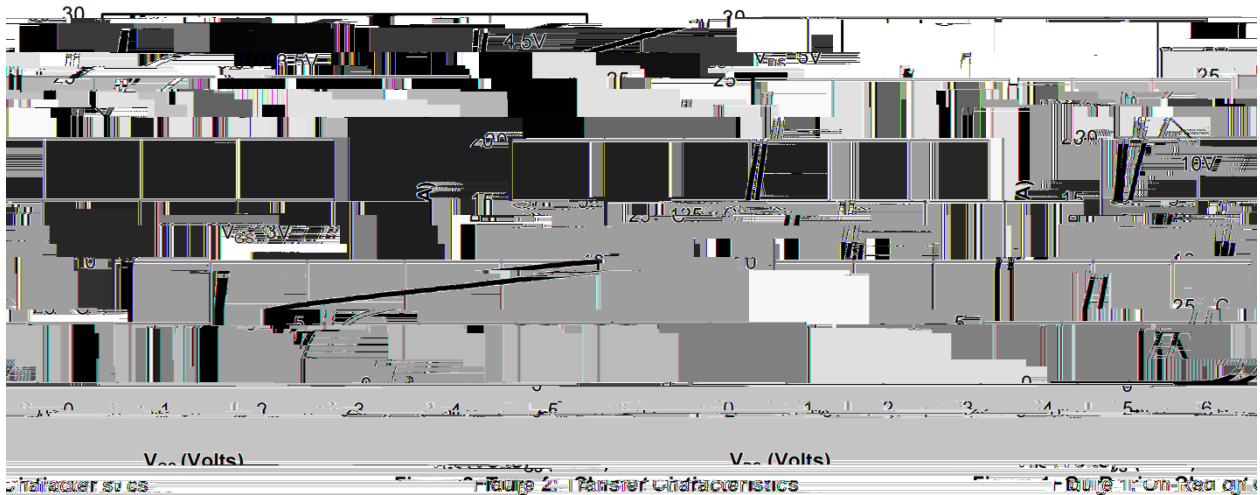
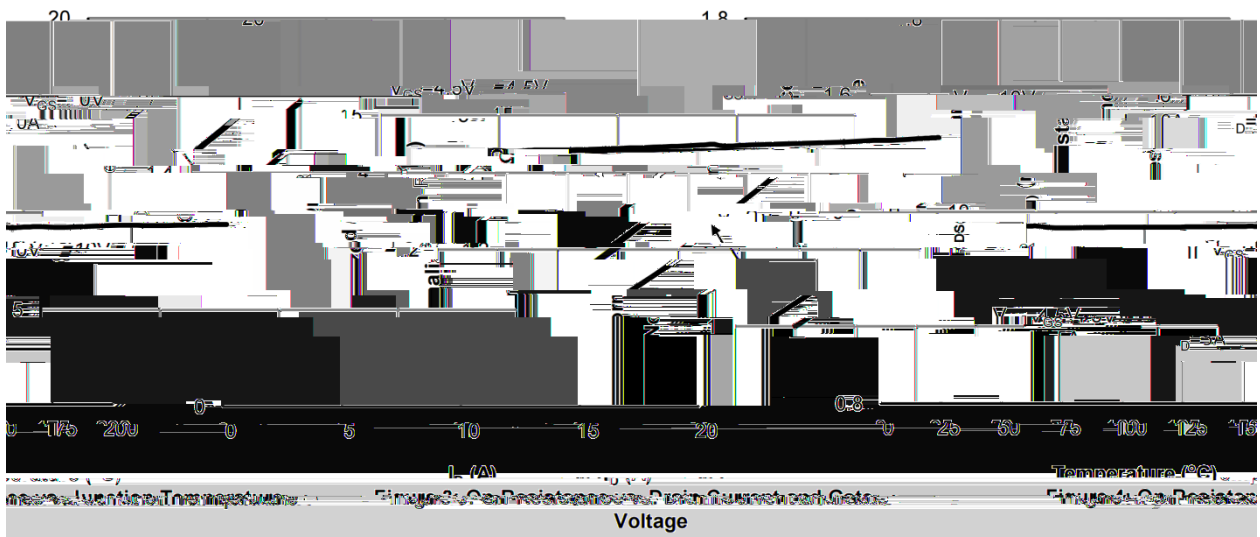
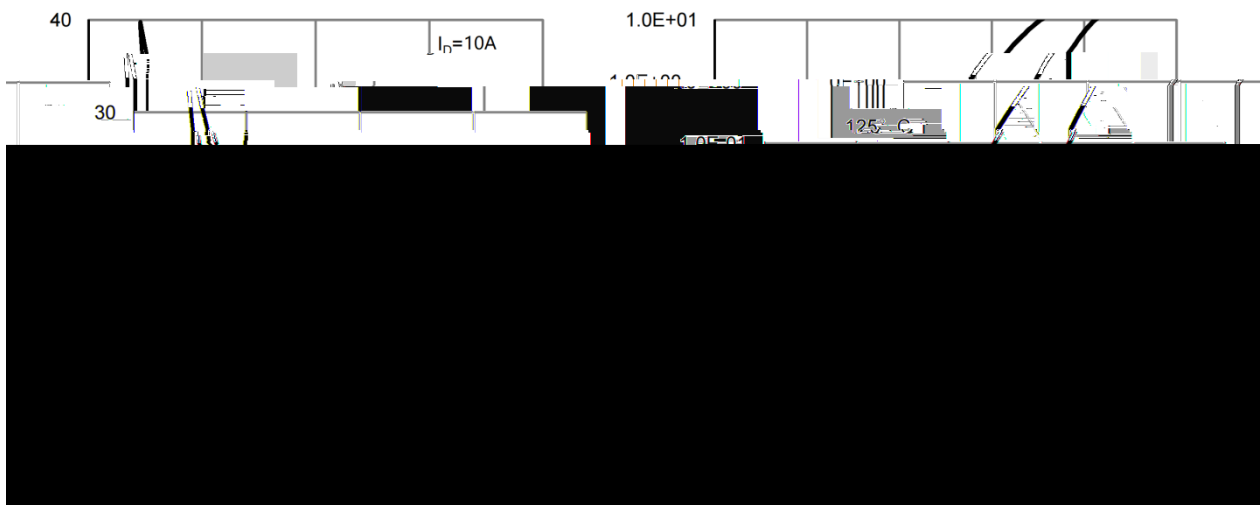
 $V_{DS}(V)=-30V$ $I_D=-39A$ $R_{DS(ON)}<12m\Omega(V_{GS}=-10V)$ $R_{DS(ON)}<20m\Omega(V_{GS}=-4.5V)$

DC/DC

These devices are well suited for 1

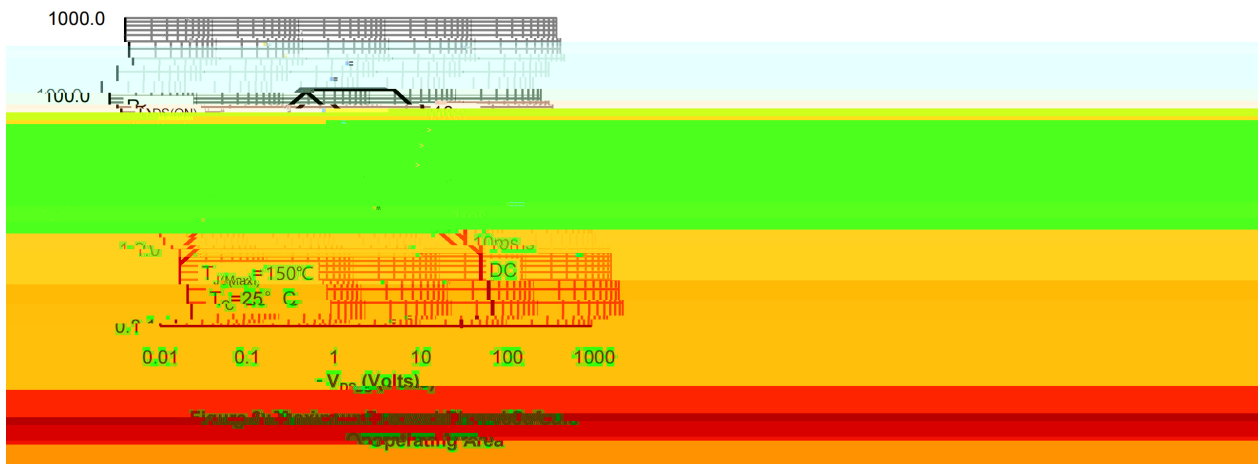
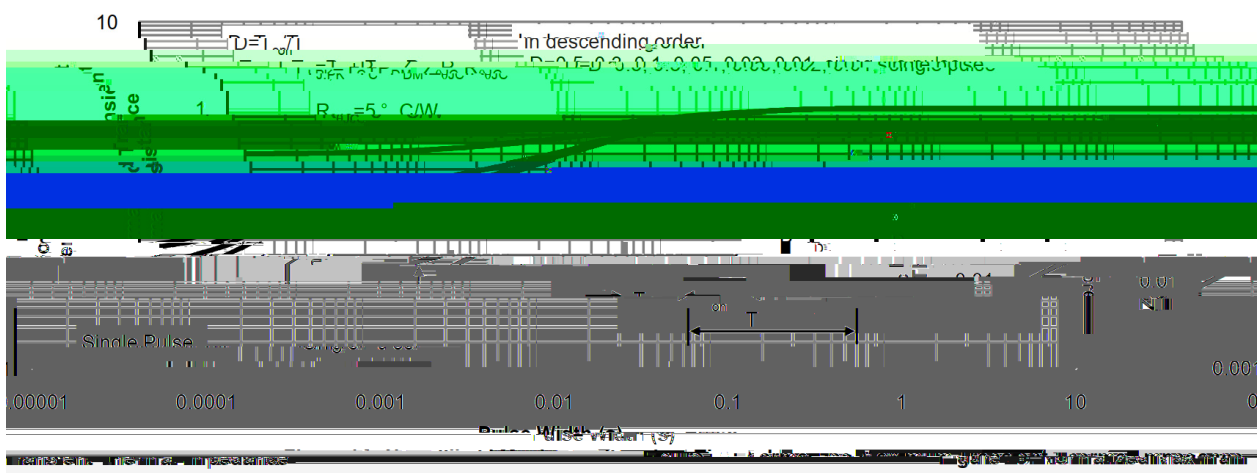
Parameter

N-

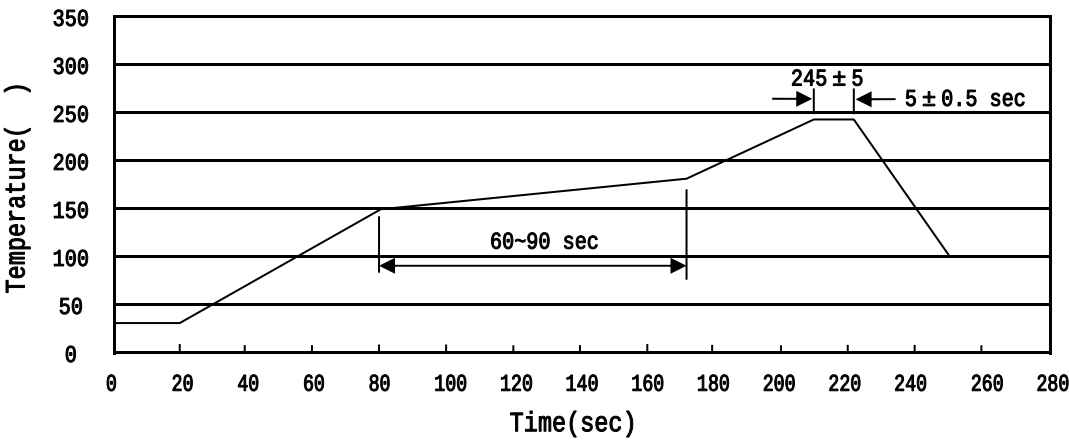


Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown						

P-



Temperature Profile for IR Reflow Soldering(Pb-Free)



Note:

- 1

150 180

60 90sec;

1.Preheating:150~180 , Time:60~90sec.
- 2

245±5

5±0.5sec;

2.Peak Temp.:245±5 , Duration:5±0.5sec.
- 3

2 10 /sec.

3. Cooling Speed: 2~10 /sec.

260±5

10±1 sec.

Temp.:260±5

Time:10±1 sec

/ REEL

Package Type	Units					Dimension (unit mm ³)		
	Units/Reel /	Reels/Inner Box /	Units/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Reel	Inner Box	Outer Box
PDFN5×6A	5,000	2	10,000	6	60,000	13"×12	360×360×50	380×335×366